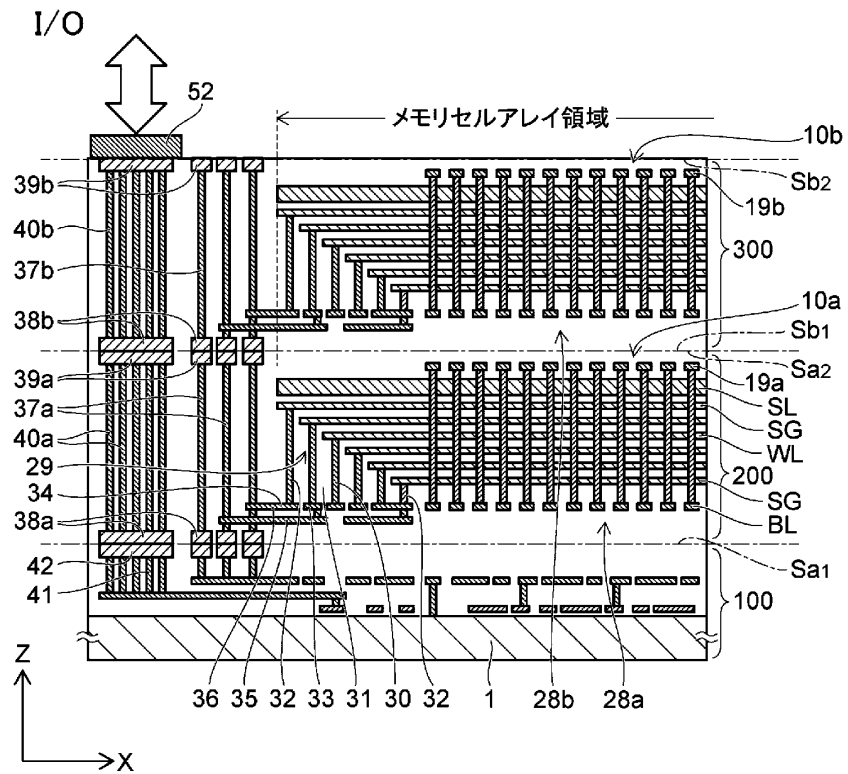
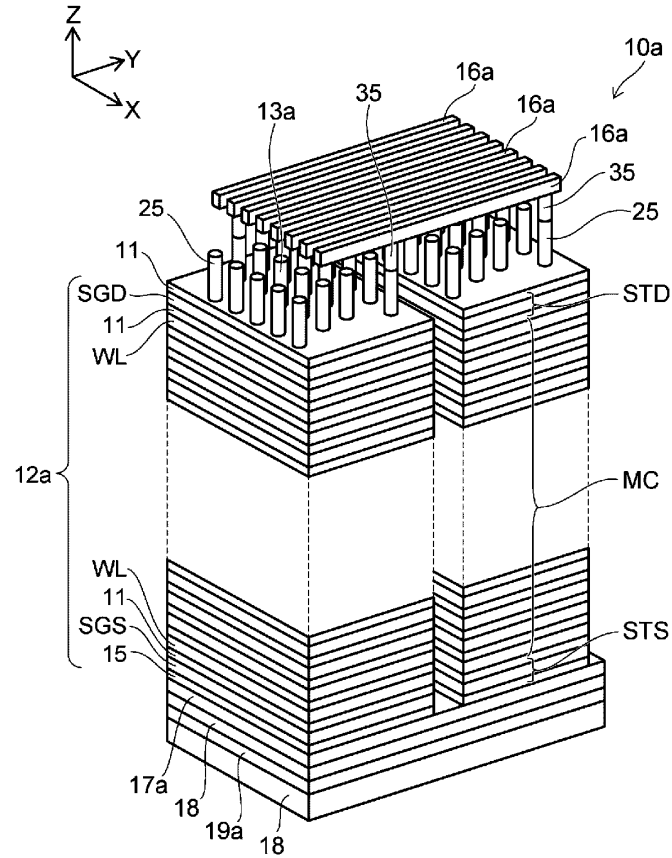


[図1]

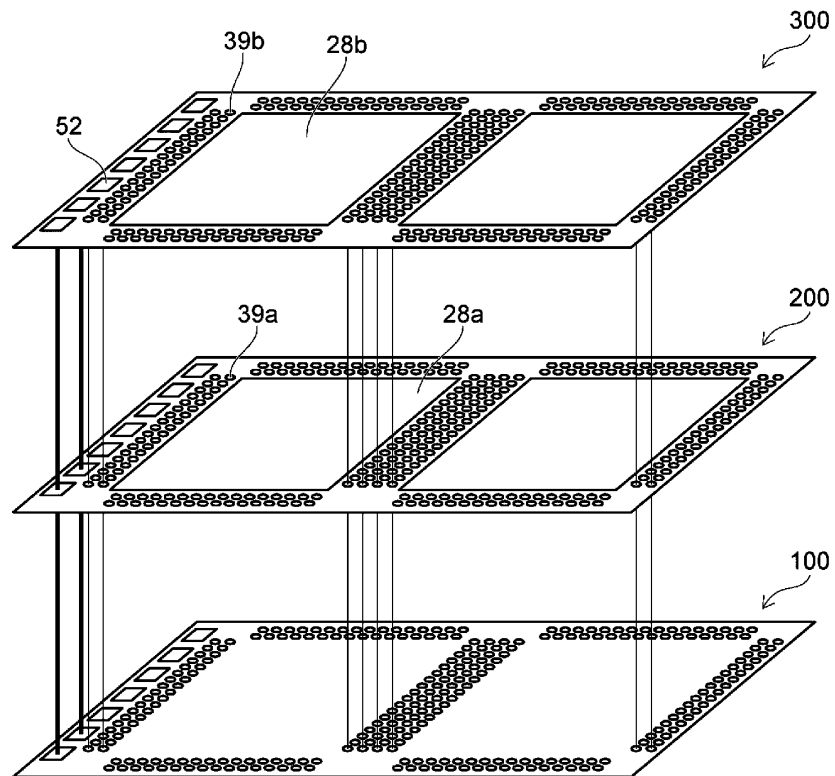


[図2]

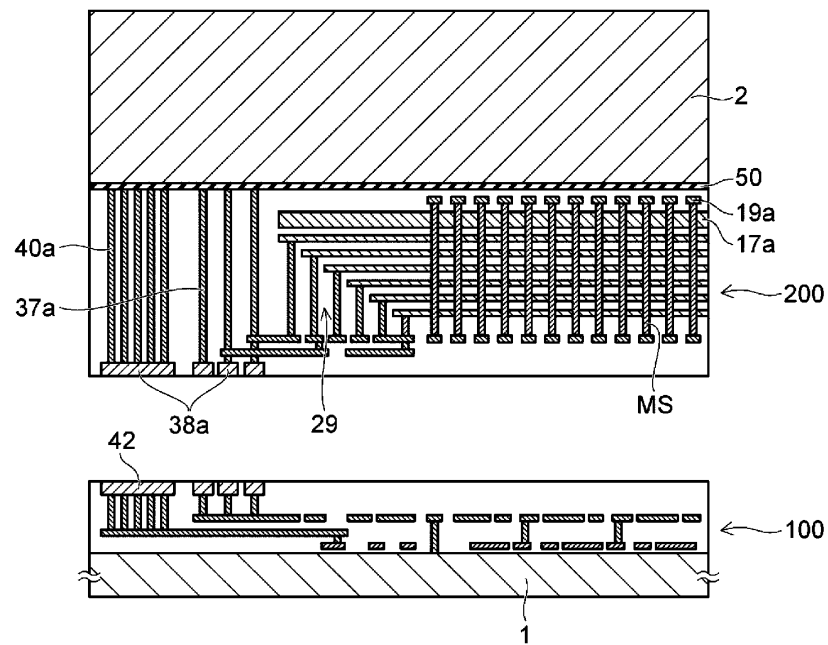


This cross-sectional view shows a semiconductor device with a stack of layers. From top to bottom, the layers are labeled 16a, 14, 20, 11, SGD, 26, 11, WL, 11, WL, 11, SGS, 27, 13a, 15, 17a, and 18. Two vertical structures are shown, each consisting of a central core (35 and 25) surrounded by a sheath (13a and 15). The structures are connected to a bottom layer (19a) via a contact (21). A dashed line A indicates a cross-section through the device. A coordinate system with Z and Y axes is shown at the bottom left.

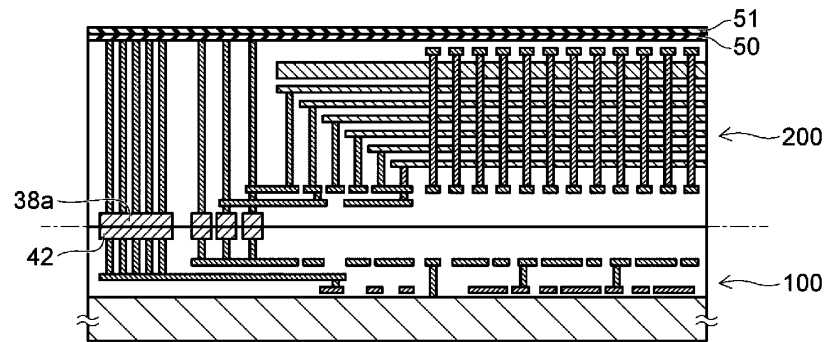
[図5]



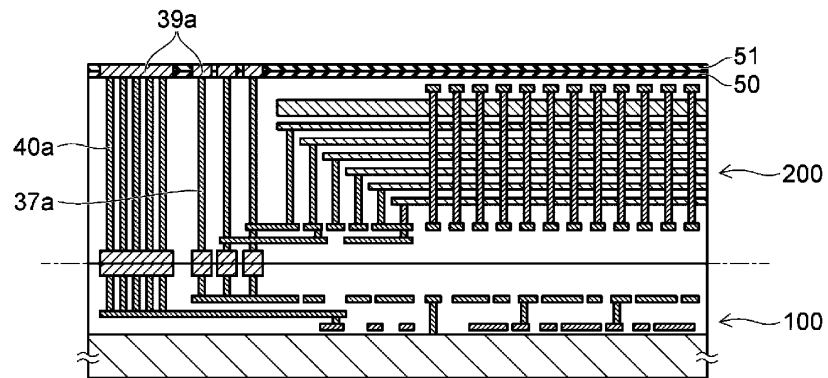
[図6]



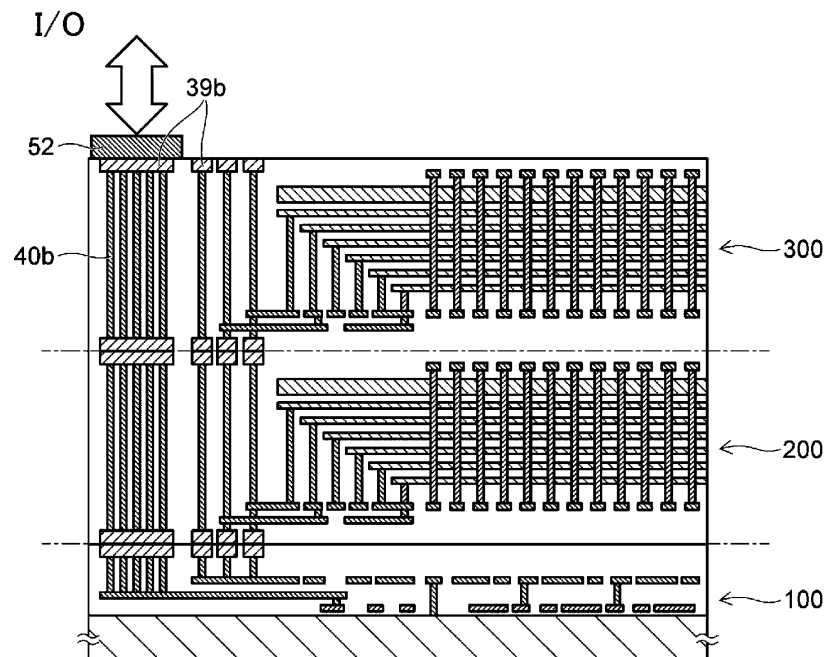
[図7]



[図8]



[図9]



I/O

MS2

300

16b

61

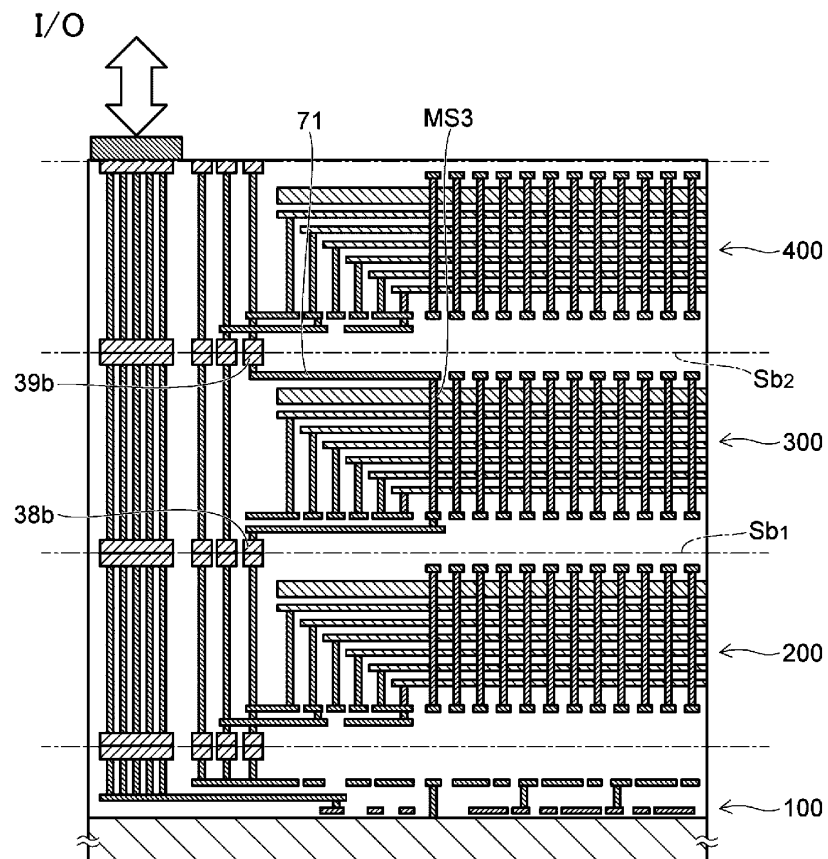
19a

MS1

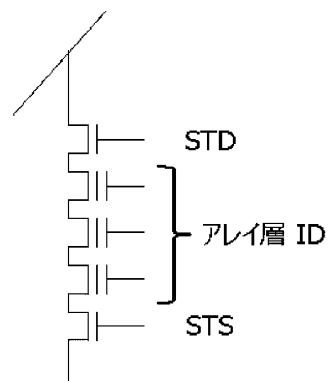
200

100

[図12]



[図13]



[図14]

